

--13. (New) The semiconductor device according to claim 1, wherein a thickness of the Ta film is 5 nm or less.

14. (New) The semiconductor device according to claim 13, wherein a thickness of the Ta film is 20 nm or more.

15. (New) The semiconductor device according to claim 13, wherein a thickness of the Ta film is 40 nm or more.

16. (New) A semiconductor device comprising:
a Cu film provided above a main surface of a semiconductor substrate and used as a wiring;
an intermediate layer formed at least on the Cu film, the intermediate layer comprising a TaN film formed on the Cu film and a Ta film formed on the TaN film, and
an Al film formed on the Ta film and used as a pad, the Al film having an extending portion under which the Cu film is not formed; and
a conductive connection member connected to the Al film at the extending portion.

17. (New) The semiconductor device according to claim 16, wherein the intermediate layer has a first portion which contacts the Cu film and a second portion which does not contact the Cu film, and an insulating film contacts the second portion.

18. (New) The semiconductor device according to claim 16, wherein the intermediate layer has a portion corresponding to the extending portion.

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